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(54) Titre : PROCÉDE DE TRAITEMENT THERMIQUE LATERAL DE FILMS MINCES SUR DES SUBSTRATS A BASSE TEMPERATURE  
 (54) Title: METHOD FOR PROVIDING LATERAL THERMAL PROCESSING OF THIN FILMS ON LOW-TEMPERATURE SUBSTRATES

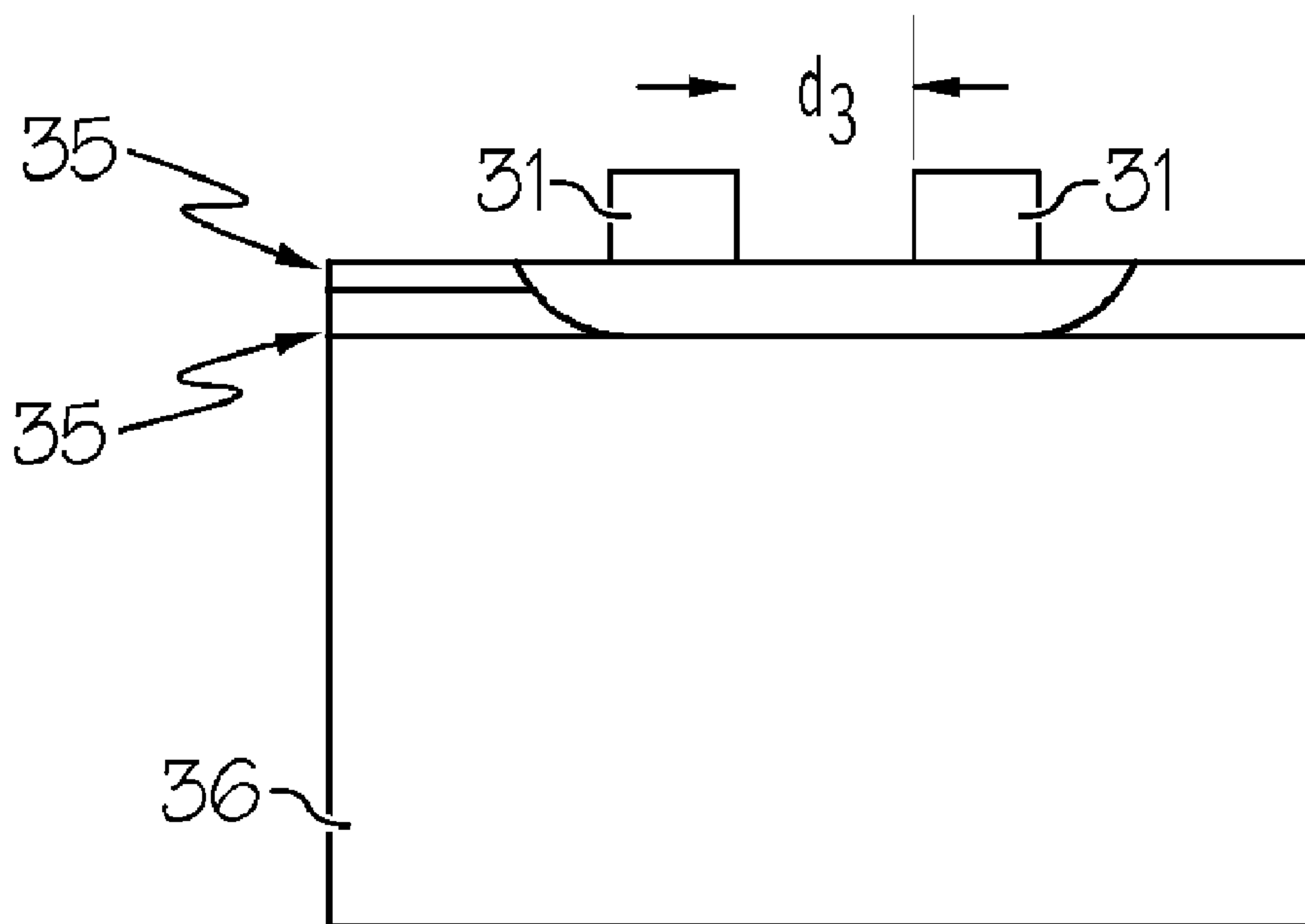


FIG. 3B

(57) Abrégé/Abstract:

A method for thermally processing a minimally absorbing thin film in a selective manner is disclosed. Two closely spaced absorbing traces are patterned in thermal contact with the thin film. A pulsed radiant source is used to heat the two absorbing traces, and the thin film is thermally processed via conduction between the two absorbing traces. This method can be utilized to fabricate a thin film transistor (TFT) in which the thin film is a semiconductor and the absorbers are the source and the drain of the TFT.

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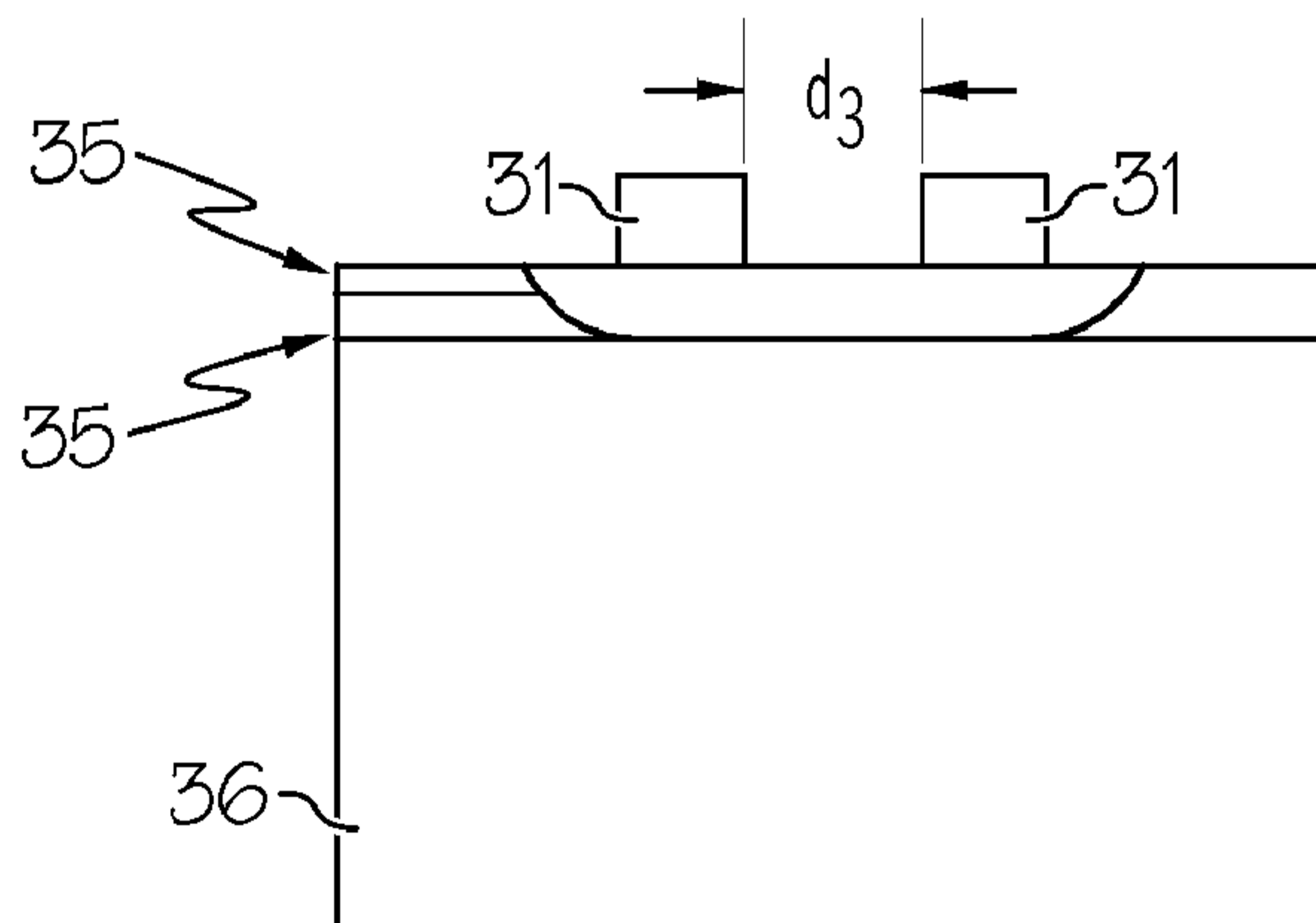
(54) Title: METHOD FOR PROVIDING LATERAL THERMAL PROCESSING OF THIN FILMS ON LOW-TEMPERATURE  
SUBSTRATES

FIG. 3B

(57) Abstract: A method for thermally processing a minimally absorbing thin film in a selective manner is disclosed. Two closely spaced absorbing traces are patterned in thermal contact with the thin film. A pulsed radiant source is used to heat the two absorbing traces, and the thin film is thermally processed via conduction between the two absorbing traces. This method can be utilized to fabricate a thin film transistor (TFT) in which the thin film is a semiconductor and the absorbers are the source and the drain of the TFT.

WO 2011/153357 A1

1           **METHOD FOR PROVIDING LATERAL THERMAL PROCESSING OF THIN**  
2                           **FILMS ON LOW-TEMPERATURE SUBSTRATES**

3  
4  
5                           **PRIORITY CLAIM**

6                           The present application claims priority under 35 U.S.C. § 119(e)(1) to  
7                           provisional application number 61/350,765 filed on June 2, 2010, the contents of which are  
8                           incorporated herein by reference.

9                           **BACKGROUND OF THE INVENTION**

10                          **1. Technical Field**

11                          The present invention relates to a method for curing thin films on substrates  
12                          in general, and, in particular, to a method for thermally processing thin films on low-  
13                          temperature substrates.

14                          **2. Description of Related Art**

15                          In general, thermal processing encompasses sintering, annealing, curing,  
16                          drying, crystallization, polymerization, chemical reaction initiation and modulation, dopant  
17                          drive-in, degasification, etc. Thermal processing of semiconductor thin films is typically  
18                          performed in high temperature environments. For example, amorphous silicon (a-Si) is  
19                          annealed at 1,100 °C, and silicon nanoparticle films are sintered at 900 °C. Thus, the  
20                          high-temperature requirement for processing semiconductor thin films often mandates the  
21                          usage of high-temperature substrates, such as fired ceramics or quartz, as the choice  
22                          substrates for carrying semiconductor thin films.

23                          Needless to say, it is more desirable to use low-temperature substrates, such  
24                          as borosilicate or soda lime, as the choice substrates for carrying semiconductor thin films  
25  
26  
27

1 if possible because of their relatively low cost. Even more desirable substrate materials  
2 would be plastic (*i.e.*, polycarbonate, polyimide, PET, PEN, etc.) or paper because their  
3 cost is even lower.

4  
5 However, the usage of equipment that can provide an equilibrium process,  
6 such as an oven, is not a viable option for thermally processing a semiconductor thin film  
7 on a low-temperature substrate. This is because the required temperature for annealing and  
8 sintering most, if not all, semiconductor thin films are considerably higher than the  
9 maximum working temperatures of low-temperature substrates such as polyimide and PET,  
10 which are around 450 °C and 150 °C, respectively.

11  
12 The present disclosure provides a method for thermally processing thin films  
13 on low-temperature substrates.

**SUMMARY OF THE INVENTION**

1  
2  
3 In accordance with a preferred embodiment of the present invention, two  
4 absorbing traces spaced apart are in thermal contact with a thin film located on top of a  
5 substrate. Pulsed radiation is utilized to heat the two absorbing traces, and the heat from  
6 the two absorbing traces is subsequently conducted in the plane of the thin film to the thin  
7 film between the two absorbing traces to thermally process the thin film.

8  
9 The above-mentioned process may be used to fabricate a thin film transistor  
10 (TFT). For example, two absorbing traces, which may be composed of metal or ceramic,  
11 can be used to form a source and drain of a TFT, and a semiconductor thin film can be  
12 used to form an active channel of the TFT.

13  
14 All features and advantages of the present invention will become apparent  
15 in the following detailed written description.

## BRIEF DESCRIPTION OF THE DRAWINGS

1  
2  
3 The invention itself, as well as a preferred mode of use, further objects, and  
4 advantages thereof, will best be understood by reference to the following detailed  
5 description of an illustrative embodiment when read in conjunction with the accompanying  
6 drawings, wherein:

7  
8 Figures **1a-1b** depict a method for thermally processing a thin film, in  
9 accordance with one embodiment of the present invention;

10  
11 Figures **2a-2b** depict a method for thermally processing a thin film, in  
12 accordance with another embodiment of the present invention;

13  
14 Figures **3a-3b** depict a method for thermally processing a very thin film on  
15 a low-temperature substrate, in accordance with one embodiment of the present invention;

16  
17 Figure **4** shows a thin film transistor (TFT) manufactured by the methods of  
18 the present invention;

19  
20 Figure **5** shows a Raman spectrum of an e-beam coated amorphous silicon  
21 on a borosilicate glass before and after being exposed to pulsed radiation;

22  
23 Figure **6** is a graph showing the selectivity of the pulsed radiation lateral  
24 thermal processing method of the present invention; and

25  
26 Figure **7** is a graph showing drain current versus drain-source voltage for the  
27 TFT from Figure **4**.

## DETAILED DESCRIPTION OF A PREFERRED EMBODIMENT

When using a pulsed radiation thermal processing technique to thermally process a thin film on a substrate, the pulsed radiation emitted from flashlamps, directed plasma arcs (DPAs), lasers, microwaves, induction heaters or electron beams has the ability to preferentially heat the thin film over its substrate. In addition, because the heat capacity of the substrate is much larger than that of the thin film, and the time of heating is much shorter than the thermal equilibration time of the substrate, the substrate can serve as a heat sink to rapidly cool the thin film immediately after thermal processing.

Although pulsed radiation thermal processing allows a thin film to be heated to a much higher temperature than its substrate can normally withstand at thermal equilibrium, such thermal processing technique generally depends on the ability of a thin film to absorb the radiation that is used to heat the thin film. Thus, when a thin film is very thin and/or somewhat transparent, it is quite difficult to thermally process the very thin film directly with the pulsed radiation thermal processing technique because the very thin film typically absorbs minimal radiation. Consequently, an improved method is required to thermally process a very thin film.

Referring now to the drawings, and in particular to Figures **1a-1b**, there are depicted a method for providing pulsed radiation thermal processing on a very thin film, in accordance with one embodiment of the present invention. Initially, a very thin film **12** is deposited on a substrate **14** via well-known vacuum techniques. Very thin film **12** may also be coated or printed on substrate **14**. Very thin film **12** can be a fully dense film or a particulate film. The thickness of very thin film **12** is preferably less than 10 microns. Next, an absorbing trace **11** is deposited on top of very thin film **12** to form a thin film stack **10**, as shown in Figure **1a**. Absorbing trace **11** is preferably made of a material that is more absorptive of pulsed radiation than very thin film **12**. Examples of absorbing trace **11** include metals or ceramics.

1           When thin film stack **10** is transiently irradiated (*i.e.*, via pulsed radiation)  
2 by a light source **15**, absorbing trace **11** is preferentially heated before very thin film **12**.  
3 Light source **15** can be a flashlamp, directed plasma arc (DPA), laser, microwave generator,  
4 induction heater or electron beam. As a result, the area (shaded area) within very thin film  
5 **12** and substrate **14** located underneath and adjacent to absorbing trace **11** is thermally  
6 processed by the heated absorbing trace **11**, as shown in Figure **1b**. The distance  $d_1$  within  
7 very thin film **12** that is thermally processed can be tens of microns.

8  
9           With reference now to Figures **2a-2b**, there are illustrated a method for  
10 providing pulsed radiation thermal processing on a very thin film, in accordance with  
11 another embodiment of the present invention. Initially, a very thin film **23** is deposited on  
12 a substrate **24** via well-known vacuum techniques. Very thin film **23** can also be coated  
13 or printed on substrate **24**. Very thin film **23** can be a fully dense film or a particulate  
14 film. The thickness of very thin film **23** is preferably less than 10 microns. Next,  
15 absorbing traces **21**, **22** are deposited on very thin film **23** to form a thin film stack **20**, as  
16 shown in Figure **2a**. Similar to absorbing trace **11** in Figure **1a**, absorbing traces **21**, **22**  
17 are preferably made of a material that is more absorptive of pulsed radiation than very thin  
18 film **23**. Examples of absorbing traces **21**, **22** include metals or ceramics. Although  
19 absorbing traces **21**, **22** are shown to be formed on top of very thin film **23**, absorbing  
20 traces **21**, **22** can be formed underneath very thin film **23** instead.

21  
22           Upon being exposed to pulsed radiation from a light source **25**, absorbing  
23 traces **21**, **22** are preferentially heated over very thin film **23**. The heat from absorbing  
24 traces **21**, **22** is then conducted to the area of very thin film **23** underneath and/or adjacent  
25 to absorbing traces **21**, **22**, as shown in Figure **2b**. In Figure **2b**, an area  $d_2$  within very  
26 thin film **23** located between absorbing traces **21**, **22** becomes thermally processed. The  
27 gap distance that can be thermally processed between absorbing traces **21** and **22** (*i.e.*, area  
28  $d_2$ ) is generally larger than  $d_1$  from Figure **1b** since it is the overlap of the heat being  
29 conducted by two absorbing traces **21**, **22** and is preferably less than 100 microns.  
30 Furthermore, since the area within very thin film **23** located between absorbing traces **21**



1 and **22** is thermally processed by the overlapping of heat being conducted from two  
2 absorbing traces **21**, **22**, very thin film **23** tends to be more uniformly processed than the  
3 area of a thin film adjacent to only one absorbing trace (such as in Figure **1b**).  
4

5 Substrate **14** in Figures **1a-1b** and substrate **24** in Figures **2a-2b** are  
6 preferably high-temperature substrates. However, thermal processing of very thin films can  
7 also be performed on low-temperature substrates (*i.e.*, maximum working temperatures of  
8 150 °C or less) by applying heat spreading films before or after the application of the  
9 absorbing traces. Since the thermal conductivity of the heat spreading film is higher than  
10 that of the low temperature substrate, heat is preferentially conducted in the plane of the  
11 very thin film and the heat spreading film instead of the low temperature substrate after  
12 absorbing traces have been heated. The heat spreading film also acts as a thermal barrier  
13 layer to protect the low temperature substrate. In addition, the preferential conduction of  
14 heat in the plane of the very thin film increases the distance at which absorbing traces can  
15 be placed from each other. As a result, a lower energy light pulse can be used to process  
16 the very thin film, thus making the process more gentle on the low-temperature substrate.  
17 The heat spreading film is generally thicker than the very thin film and is generally  
18 transparent to the light used to heat the absorbing traces.  
19

20 Referring now to Figures **3a-3b**, there are illustrated a method for thermally  
21 processing a very thin film on a low-temperature substrate, in accordance with one  
22 embodiment of the present invention. Initially, a heat spreading film **35** is deposited on a  
23 substrate **34** via well-known vacuum techniques. Heat spreading film **35** may be coated  
24 or printed on substrate **34**. A very thin film **33** is then deposited on top of heat spreading  
25 film **35** via well-known vacuum techniques. Very thin film **33** may be coated or printed  
26 on heat spreading film **35**. Very thin film **33** can be a fully dense film or a particulate  
27 film. The thickness of very thin film **33** is preferably less than 10 microns. Next,  
28 absorbing traces **31**, **32** are deposited on very thin film **33** to form a thin film stack **30**, as  
29 shown in Figure **3a**. Similar to absorbing traces **21**, **22** in Figure **2a**, absorbing traces **31**,

1 **32** are preferably made of a material that is more absorptive of pulsed radiation than very  
2 thin film **33**. Examples of absorbing traces **31**, **32** include metals or ceramics.

3  
4 Although absorbing traces **31**, **32** are shown to be formed on top of very thin  
5 film **33**, absorbing traces **31**, **32** can be formed underneath very thin film **33**. Although  
6 heat spreading film **35** is shown to be formed underneath very thin film **33**, heat spreading  
7 film **35** can be formed on top of very thin film **33** or absorbing traces **31**, **32**.

8  
9 Upon being exposed to pulsed radiation from a light source **35**, absorbing  
10 traces **31**, **32** are preferentially heated over very thin film **33** and heat spreading film **35**.  
11 The heat from absorbing traces **31**, **32** is then conducted to the area of very thin film **33**  
12 and heat spreading film **35** underneath and/or adjacent to absorbing traces **31**, **32**, as shown  
13 in Figure **3b**. In Figure **3b**, an area  $d_3$  within very thin film **33** and heat spreading film **35**  
14 located between absorbing traces **31**, **32** becomes thermally processed. The gap distance  
15 that can be thermally processed between absorbing traces **31** and **32** is preferably less than  
16 100 microns.

17  
18 There is a host of materials suitable for being heat spreading film **35**. For  
19 a low-temperature substrate such as PET, those materials may include high-temperature  
20 polymers (such as polyimide) or inorganic coatings such as sputtered metal oxides or spin  
21 on glass (SOG). For higher-temperature substrates such as polyimide, more suitable  
22 materials for heat spreading film **35** include inorganic coatings such as sputtered metal  
23 oxides or SOG. It is preferable that heat spreading film **35** be somewhat transparent in  
24 order to maintain transparency of the very thin film and still allow the selective heating to  
25 occur. The required thickness of heat spreading film **35** is a function of its thermal  
26 properties, the thickness and thermal properties of the underlying low temperature substrate,  
27 the desired processing temperature of very thin film **33**, the dimensions and spacing of  
28 absorbing traces **31**, **32**, and the input radiant heating profile.

1           One approach of applying a heat spreading film to a high-temperature  
2 substrate is to first apply a polymeric coating, which has lower thermal conductivity than  
3 the high-temperature substrate, to the high-temperature substrate followed by the application  
4 of a heat spreading film. This practice retards the diffusion of heat into the thermally  
5 conductive substrate and allows a very thin film to be processed. An alternative to the  
6 polymeric coating is to use a high-temperature, low-thermal conductivity inorganic film so  
7 that it can withstand a higher temperature during thermal processing.

8  
9           One method to achieve a high-temperature, low-thermal conductivity  
10 inorganic film is to make the inorganic film porous by using a SOG and load it with porous  
11 particles. For example, such an inorganic film can be made by using silica aerogel  
12 nanoparticles loaded in a SOG. The resulting inorganic film appears to have a thermal  
13 conductivity of the order of (or even lower than that of) PET (*i.e.*, 0.24 W/m-°K). Since  
14 the aerogel particles have the SOG matrix, the inorganic film is much more durable than  
15 a typical aerogel film.

16  
17           The thermal processing of the very thin film can be tuned by varying the  
18 power and length of the pulsed radiation. Multiple pulses can be used as well as adjusting  
19 the pulse repetition frequency. The shape of the pulse can be changed using pulse width  
20 modulation to further adjust the heating profile. When the pulse length is shorter than the  
21 thermal equilibration time of the low-temperature substrate, that is, perpendicular to the  
22 plane of the low-temperature substrate, a stronger thermal gradient and higher peak  
23 temperature can be generated in it, thereby preferentially heating the very thin film adjacent  
24 to the absorbing traces. The temperature in the very thin film is more intensely processed  
25 near the absorbing traces relative to regions farther away from the absorbing traces.  
26 Furthermore, pulsed radiation allows the peak processing temperature to be greater than the  
27 maximum equilibrium working temperature of a substrate. For example, 150 micron thick  
28 PET thermally equilibrates across its thickness in about 35 ms. Thus, a stronger thermal  
29 processing gradient as well as a higher peak temperature can be produced without damaging  
30 the low-temperature substrate with a 300  $\mu$ s pulse than with a 10 ms pulse. A 100 ms

1 pulse can still heat the very thin film located between the absorbing traces, but the peak  
2 temperature that can be maintained is very close to its maximum equilibrium working  
3 temperature of 150 °C. In sum, the maximum peak temperature that can be achieved in  
4 the very thin film without damaging the low-temperature substrate of a longer pulse is less  
5 than that of a short pulse, but the lateral processing length is correspondingly longer also.  
6 Since the thermal processing of the very thin film is usually Arrhenius in nature, *i.e.*, the  
7 thermal processing is generally related to the exponential of the processing temperature  
8 times time, a shorter pulse can process the very thin film more effectively than a longer  
9 pulse without damaging the low-temperature substrate.

10  
11 The thickness, width, and spacing of absorbing traces as well as the thickness  
12 and thermal properties of a very thin film and underlying layers also contribute to the  
13 heating profile seen by the very thin film upon being exposed by pulsed radiation.

14  
15 The method of the present invention can process very thin films that are not  
16 particularly radiation absorbing. This is particularly relevant to the fabrication of thin film  
17 transistors (TFTs) that are very desirable because of their low cost and high performance.

18  
19 Referring now to Figure 4, there is depicted a TFT **40** manufactured by the  
20 above-mentioned pulsed radiation thermal processing technique. As shown, a thin dielectric  
21 layer **44** is placed on top of two absorbing traces **41** and **42** that are located adjacent to a  
22 very thin film **43**. A conductive trace **45** is located on top of dielectric layer **44** and  
23 absorbing traces **41** and **42**. Absorbing traces **41**, **42** are electrically conductive and form  
24 the source and the drain of a TFT, respectively. Conductive trace **45** forms the gate of the  
25 TFT. The area located between absorbing traces **41** and **42** within very thin film **43** that  
26 has been thermally processed is a semiconductor forms the active channel of the TFT. As  
27 shown in Figure 4, the cured area (shaded area) includes the gate oxide and the gate.  
28 However, both the gate oxide and the gate are applied after the curing of the very thin film  
29 **43**.

1           Very thin film **43** is cured primarily between absorbing traces **41** and **42**.  
2 Thus, sources and drains can be patterned (or printed) on a very large area, and very thin  
3 film **43** can even be coated over an entire substrate **46**. Since a cured semiconductor  
4 generally has a higher conductivity than an uncured one, the fact that the semiconductor  
5 becomes cured primarily in the channel of the TFT, the parasitic capacitance of the  
6 semiconductor is reduced. The reduced need for registration and critical dimensions means  
7 that the above-mentioned TFT can be completely printed *en mass*.

8  
9           An example of a method for making a TFT, such as TFT **40**, is described  
10 as follows. When making a TFT, microcrystalline silicon ( $\mu\text{x-Si}$ ) is more desirable as a  
11 semiconductor than amorphous silicon (a-Si) because  $\mu\text{x-Si}$  has higher mobility and  
12 therefore enables a faster switching TFT. It is usually easier to deposit a-Si followed by  
13 a thermal anneal to convert a-Si to  $\mu\text{x-Si}$  than to deposit  $\mu\text{x-Si}$  directly. For example, a  
14 200 nm film of a-Si on a 500  $\mu\text{m}$  borosilicate wafer can be converted to  $\mu\text{x-Si}$  (with an N<sub>2</sub>  
15 purge) by using a light pulse from a PulseForge<sup>®</sup> 3300 system (manufactured by  
16 NovaCentrix in Austin, Texas) at a threshold voltage of 650 V and a pulse length of 100  
17  $\mu\text{s}$ . The light pulse has an intensity of about 35 kW/cm<sup>2</sup>, which corresponds to a radiant  
18 exposure of about 3.5 J/cm<sup>2</sup>.

19  
20           With reference now to Figure **5**, there is illustrated a Raman spectrum of 200  
21 nm a-Si film that was e-beam sputtered coated on a borosilicate glass before and after being  
22 exposed to the above-mentioned light pulse. The a-Si film is annealed by the light pulse  
23 and is converted to  $\mu\text{x-Si}$ . The light pulse is needed to overcome the fact that a 200 nm  
24 a-Si coating only absorbs a portion of the emitted light.

25  
26           An identical borosilicate wafer is patterned with gold contact source/drain  
27 lines to form an eventual TFT of various widths (5-50  $\mu\text{m}$ ) and separations (5-50  $\mu\text{m}$ ). All  
28 traces are 5 mm long. The gold patterning is followed by an identical broadcast electron  
29 beam sputtered deposition of 200 nm of a-Si described above over the borosilicate wafer.  
30 The borosilicate wafer is then processed via the above-mentioned PulseForge<sup>®</sup> 3300 system

1 at a much lower voltage (*i.e.*, 550 V for 250  $\mu$ s). The radiant power was 24 kW/cm<sup>2</sup>, and  
2 the radiant exposure was 5.9 J/cm<sup>2</sup>. Note that this level of power is below the threshold  
3 intensity described above for converting a-Si to  $\mu$ x-Si. Since gold is very absorbing of the  
4 light pulse, more energy is absorbed at those locations.

5  
6 Referring now to Figure 6, there is illustrated the selectivity of the pulsed  
7 radiation thermal processing method of the present invention. The graph shows a  
8 comparison of the Raman spectrum of the thin silicon film between two different gold line  
9 pair widths (50  $\mu$ m and 20  $\mu$ m) and identical spacing (50  $\mu$ m) between the gold traces.  
10 The graph shows that the space between the 50  $\mu$ m traces has been converted to  $\mu$ x-Si,  
11 whereas the space between the 20  $\mu$ m wide traces is unconverted. Similarly, the silicon  
12 film on the rest of the wafer is unconverted. This technique has converted the a-Si to  $\mu$ x-Si  
13 only between the gold patterned traces and nowhere else achieving automatic registration.

14  
15 After selective conversion of a-Si to  $\mu$ x-Si between the absorbing traces has  
16 been achieved, a TFT device can be fabricated using a spin-on barium-strontium-titanate  
17 (BST) ceramic as the dielectric layer. This dielectric material has a relatively high  
18 dielectric constant  $k$  ( $\sim$ 300), which allows a high electric field to be imparted to the  
19 field-effect channel of the TFT at low gate voltage. A silver gate metal is vacuum  
20 deposited onto the BST gate dielectric layer to complete the TFT.

21  
22 Electrical testings can be performed on the TFT to determine if the drain  
23 current can be enhanced by applying a positive gate voltage. Since  $\mu$ x-Si is slightly n-type,  
24 a positive gate voltage should enhance the electron concentration in the channel and result  
25 in an increased drain current ( $I_d$ ).

26  
27 With reference now to Figure 7, there is illustrated a graph showing drain  
28 current ( $I_d$ ) versus drain-source voltage ( $V_{ds}$ ) for TFT 40 from Figure 4. Note that at  
29 positive gate voltage ( $V_g$ ), the drain current ( $I_d$ ) is enhanced and has the saturation shape  
30 one expects for a field-effect TFT. The linear I-V characteristic observed at negative gate

1 voltage indicates TFT 40 is behaving as a regular resistor when the negative gate voltage  
2 is applied. Reasons for this are unknown at this time but may be due to hole injection  
3 from the source and drain contacts. This effect, if present, is normally reduced/eliminated  
4 by suitably doping the contact regions in order to "block" hole injection.  
5

6 In summary, using pulsed light annealing of an a-Si thin film with laterally  
7 positioned metal source-drain contacts can be "sub-threshold" annealed to a microcrystalline  
8 state within the region between the source-drain contacts. This has great benefit for the  
9 microelectronics industry since micro (and nano)-crystalline silicon films have high carrier  
10 mobility and other desirable features that enhance the performance of thin film devices.  
11 Furthermore, since one can convert only the a-Si in the region between source/drain  
12 contacts, leaving the surrounding regions of the a-Si to remain in a high-resistance  
13 amorphous state, and thus not require patterning or otherwise isolation to limit such  
14 deleterious effects as parasitic capacitances which limit device speed and increase power  
15 dissipation.  
16

17 As has been described, the present invention provides a method for thermally  
18 processing thin films on low-temperature substrates. The method of the present invention  
19 also enables a TFT to be manufactured in a top gate configuration (*i.e.*, gate on top) with  
20 minimal registration. Two absorbing traces form a source and drain of a TFT. Before the  
21 application of the gate oxide and the gate, the thin film material is preferentially thermally  
22 processed between the two absorbing traces. The method of the present invention has the  
23 effect of selectively curing the thin film material without the need to precisely deposit the  
24 material in the channel of the TFT.  
25

26 While the invention has been particularly shown and described with reference  
27 to a preferred embodiment, it will be understood by those skilled in the art that various  
28 changes in form and detail may be made therein without departing from the spirit and scope  
29 of the invention.

**CLAIMS**

What is claimed is:

1. A method for thermally processing a very thin film, said method comprising:
  - patterning two absorbing traces on top of a very thin film, wherein said thin film is located on top of a substrate;
  - irradiating said two absorbing traces with at least one electromagnetic pulse to heat up said two absorbing traces; and
  - allowing heat from said two absorbing traces to thermally process said very thin film.



2. The method of Claim 1, wherein said substrate has a maximum working temperature of less than 450 °C.
3. The method of Claim 1, wherein said two absorbing traces are made of materials more absorptive of said electromagnetic pulse than said very thin film.
4. The method of Claim 1, wherein said two absorbing traces are made of metal.
5. The method of Claim 1, wherein said two absorbing traces are made of ceramic.
6. The method of Claim 1, wherein said method further includes providing a heat spreading layer between said very thin film and said substrate.
7. The method of Claim 1, wherein said electromagnetic pulse is provided from a flashlamp.
8. The method of Claim 1, wherein said electromagnetic pulse is provided from a directed plasma arc.

9. A method for fabricating a thin film transistor, said method comprising:

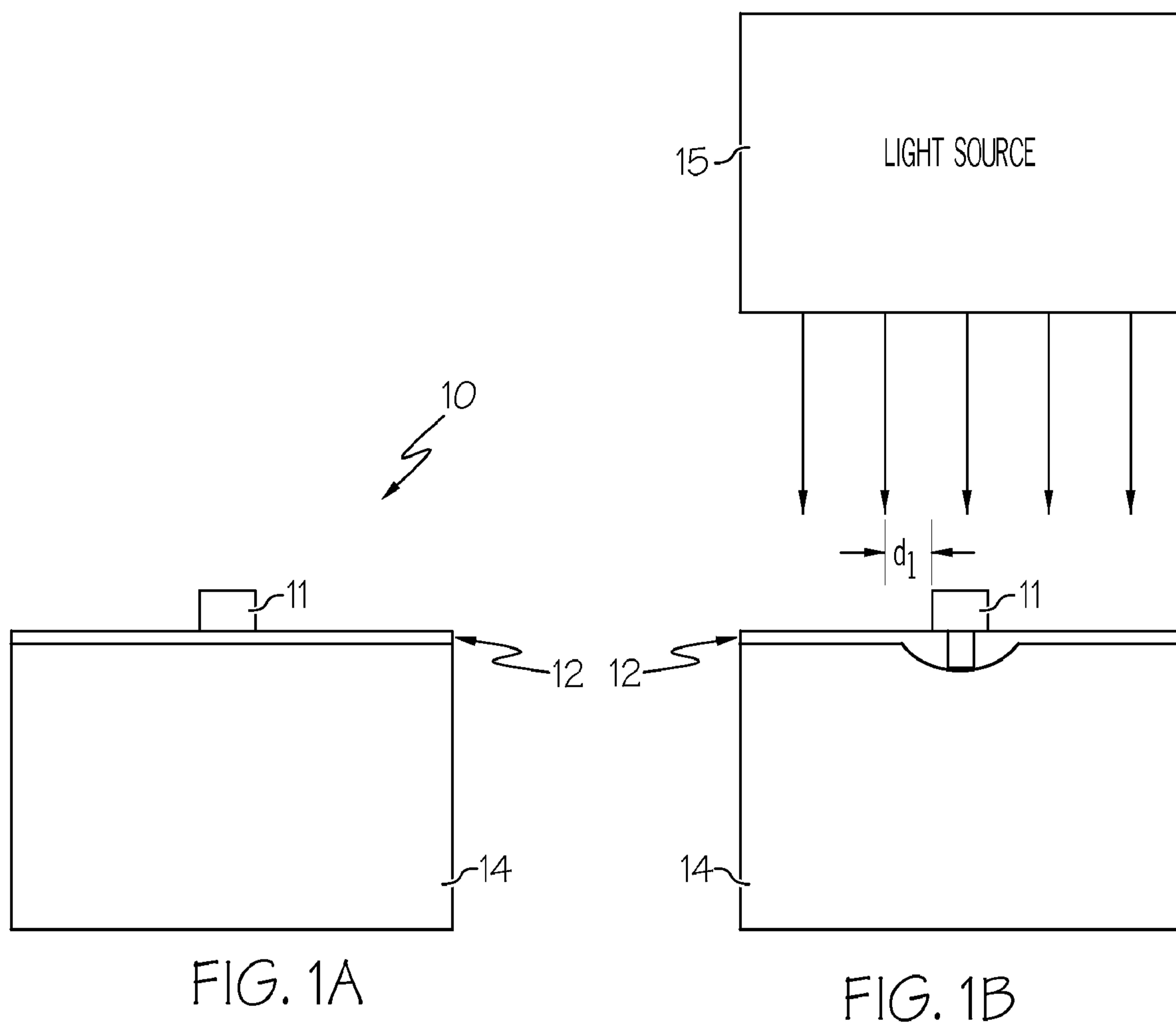
patterning two absorbing traces adjacent to a very thin film, wherein said thin film is located on top of a substrate;

irradiating said two absorbing traces with at least one electromagnetic pulse to heat up said two absorbing traces, and allowing heat from said two absorbing traces to thermally process said very thin film;

depositing a dielectric layer on said two absorbing trace and said very thin film; and

forming a gate by depositing a conductive trace on top of said dielectric layer.

10. The method of Claim 9, wherein said substrate has a maximum working temperature of less than 450 °C.
11. The method of Claim 9, wherein said two absorbing traces are made of materials more absorptive of said electromagnetic pulse than said very thin film.
12. The method of Claim 9, wherein said two absorbing traces are made of metal.
13. The method of Claim 9, wherein said two absorbing traces are made of ceramic.
14. The method of Claim 9, wherein said method further includes providing a heat spreading layer between said very thin film and said substrate.
15. The method of Claim 14, wherein said method further includes providing a high-temperature, low-thermal conductivity film between said heat spreading layer and said substrate.
16. The method of Claim 9, wherein said electromagnetic pulse is provided from a flashlamp.
17. The method of Claim 9, wherein said electromagnetic pulse is provided from a directed plasma arc.



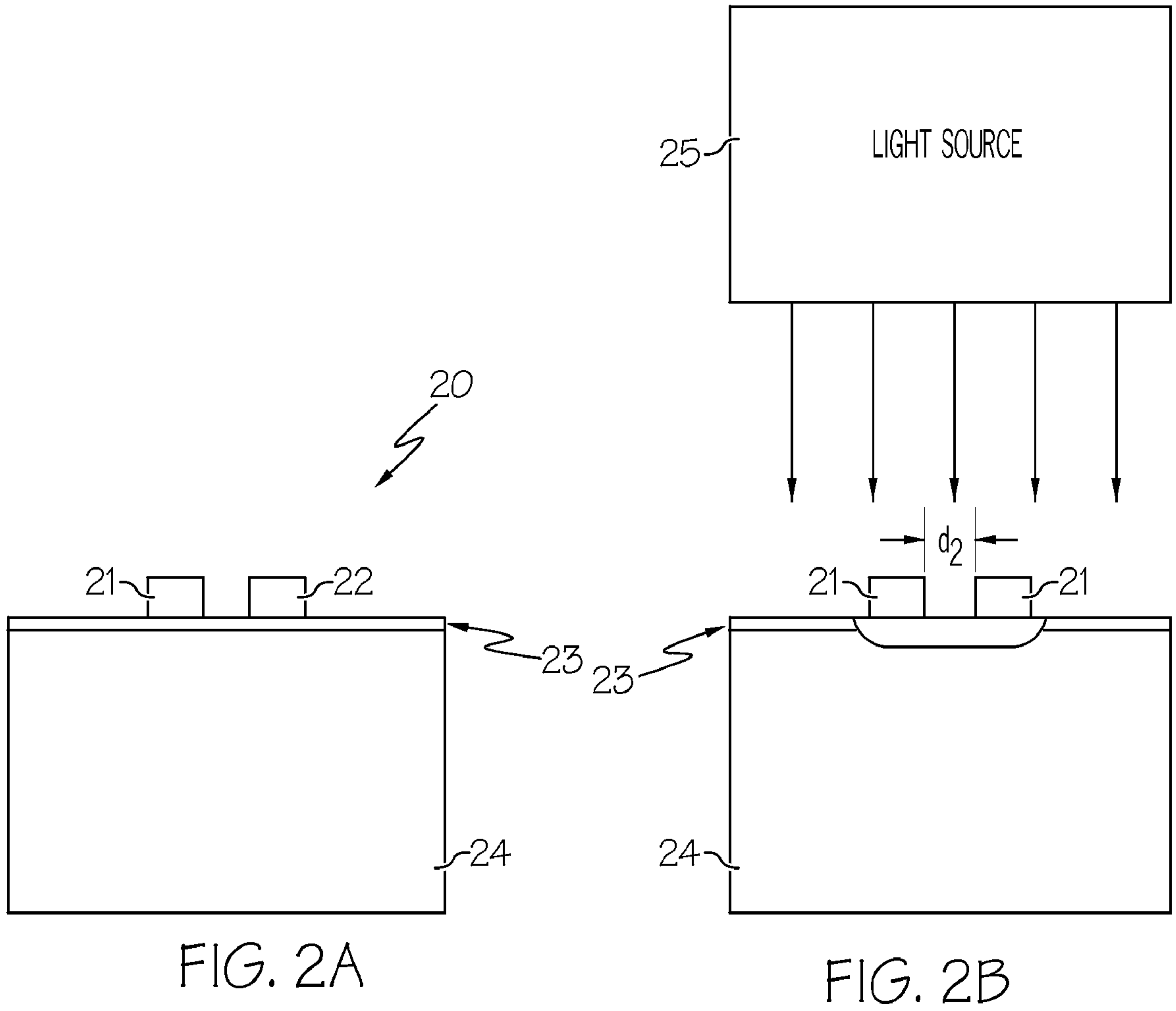


FIG. 2A

FIG. 2B

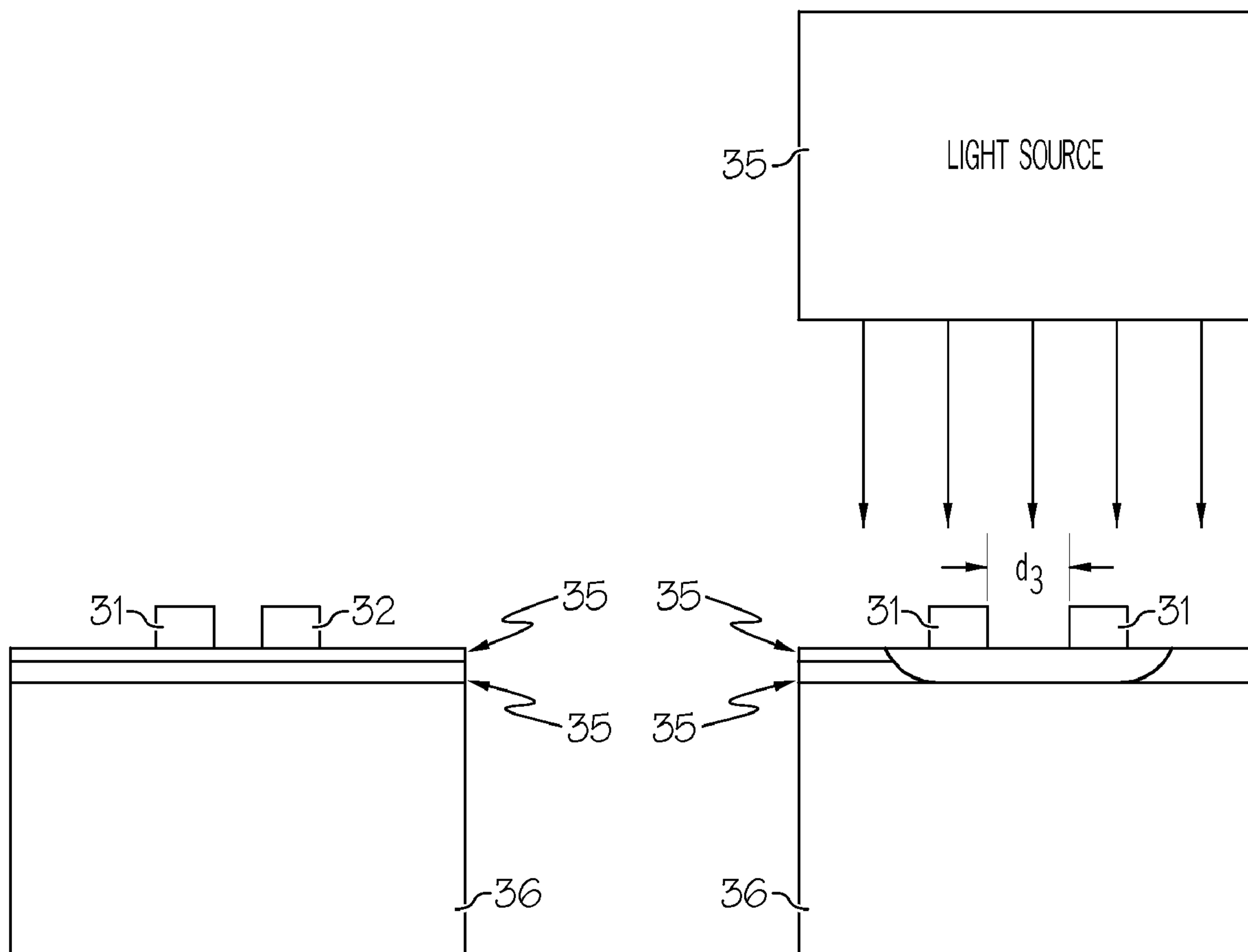


FIG. 3A

FIG. 3B

4 / 5

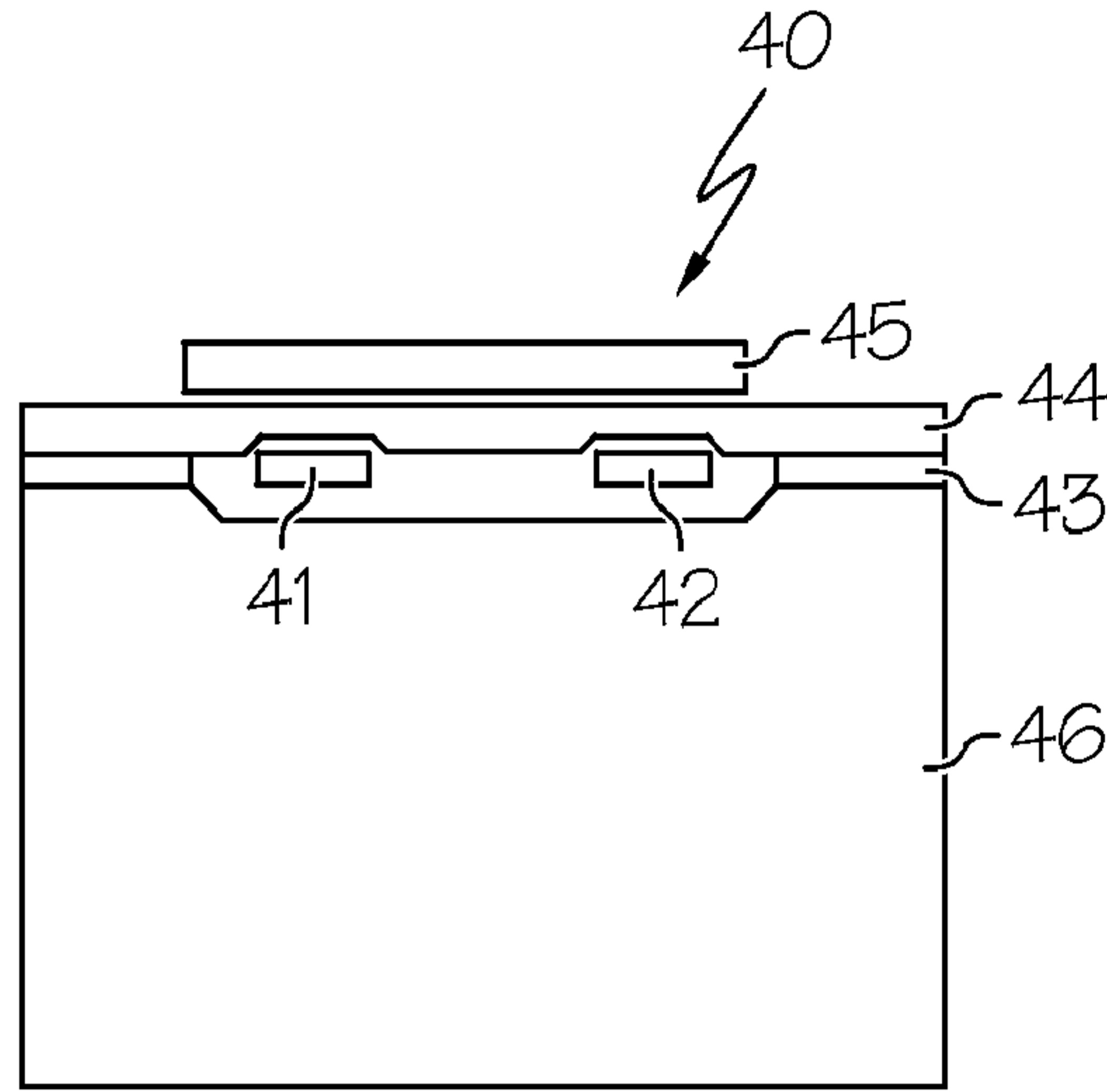


FIG. 4

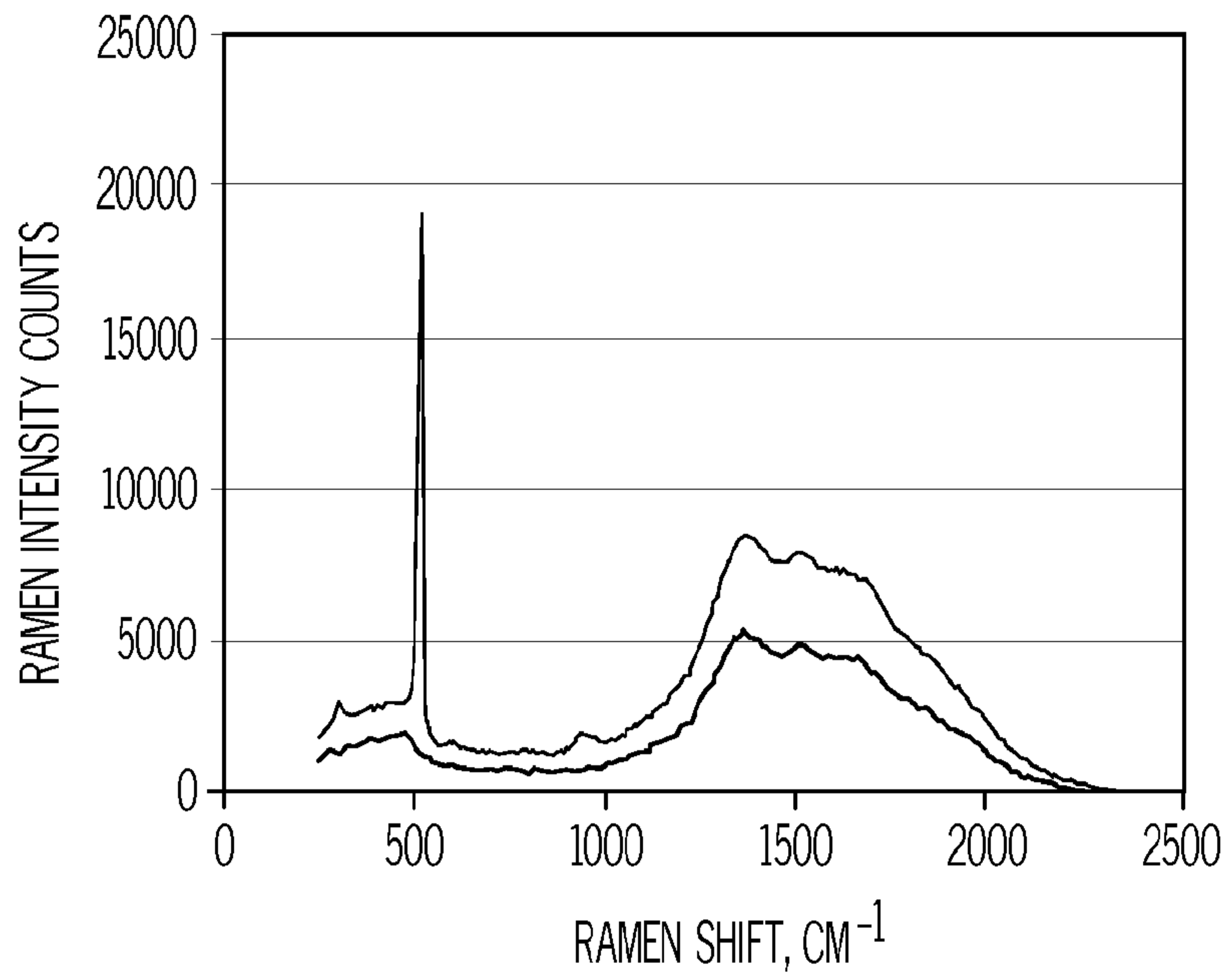


FIG. 5

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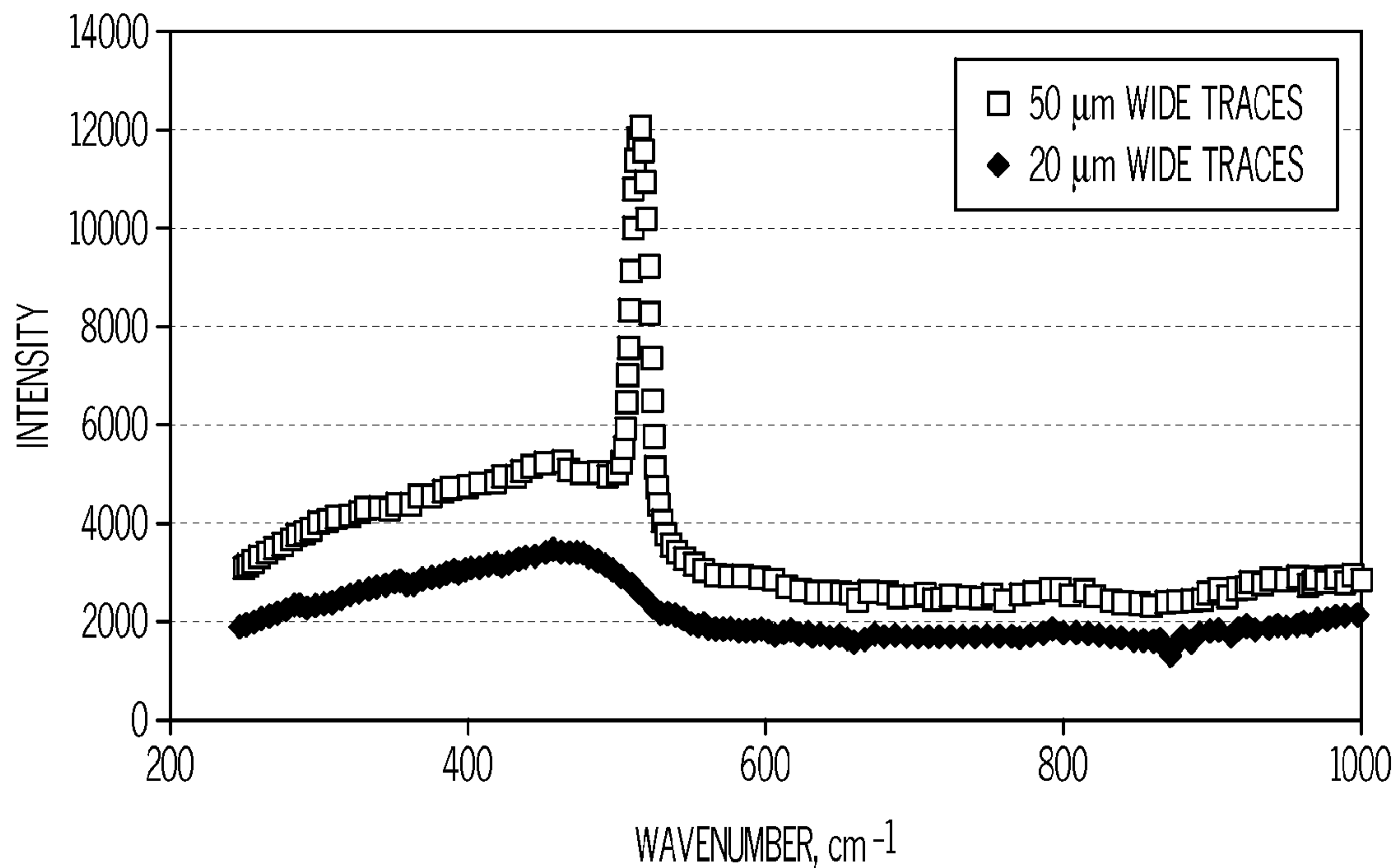


FIG. 6

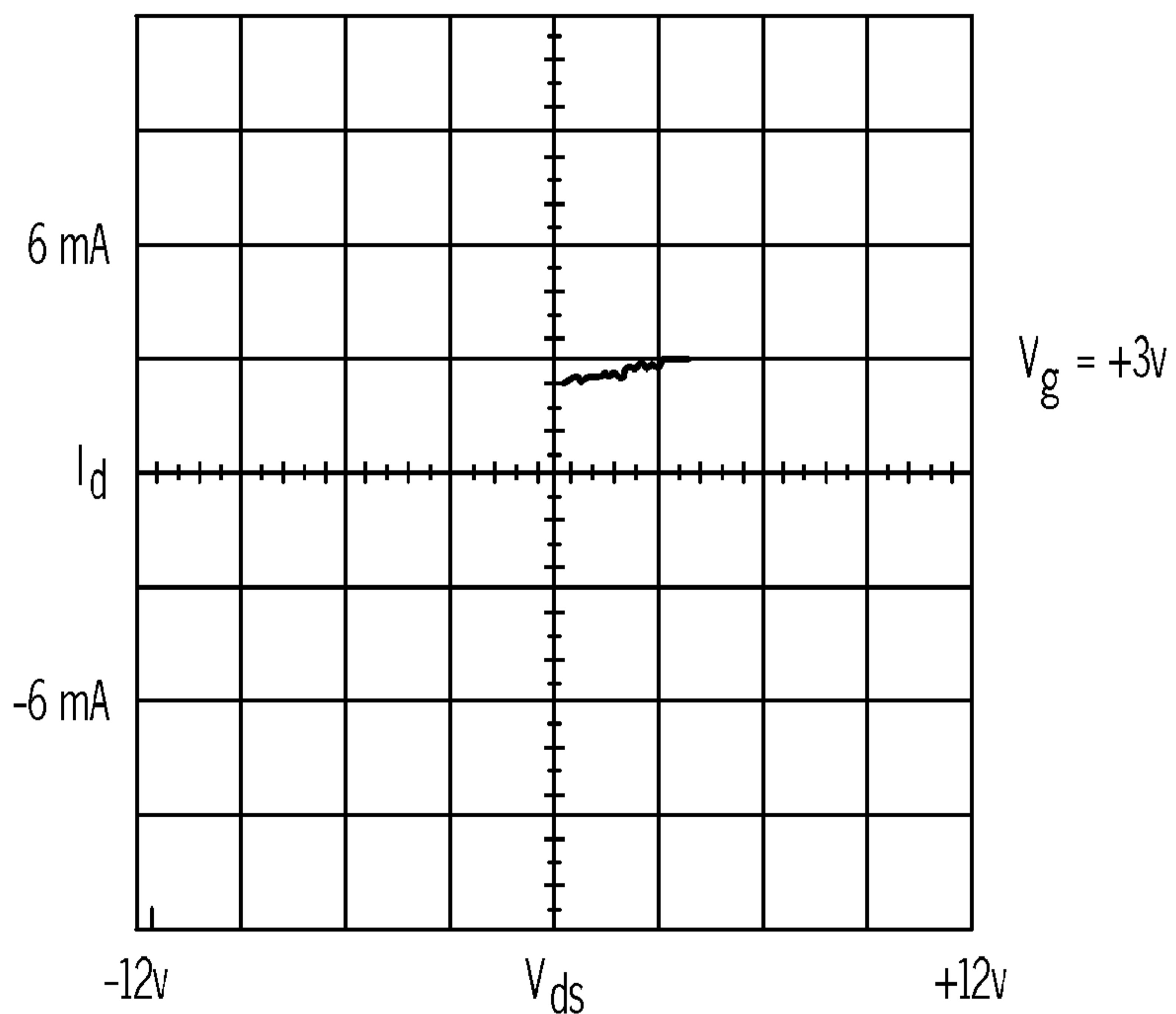


FIG. 7



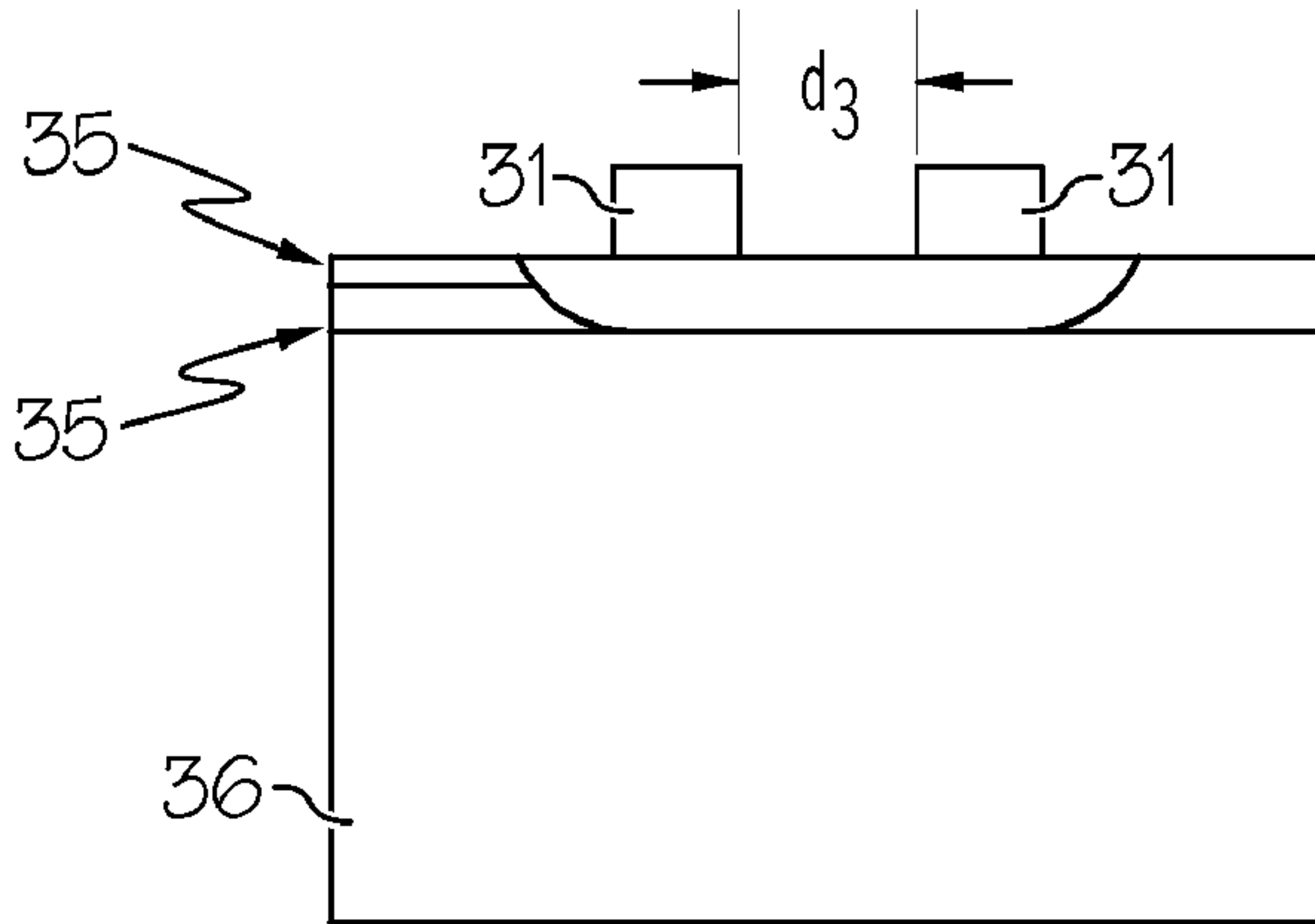


FIG. 3B